METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE

ABSTRACT OF THE DISCLOSURE

When printing is performed on a base substrate with a laser after a single crystal silicon layer is transferred to the base substrate, there are problems such as ablation of the single crystal silicon layer in the peripheral portion of a printed dot or attachment of glass chips or the like to the surface of the single crystal silicon layer. After printing is performed on the bonding surface of a silicon wafer with a laser, the surface of the silicon wafer is polished by CMP (chemical mechanical polishing), so that the projection in the peripheral portion of the printed dot is removed. After that, the silicon wafer is bonded to the base substrate. Since the depression of the printed dot remains to some extent by a chemical etching effect even after the polishing by CMP, the single crystal silicon layer is not transferred only at the depression portion at the time of the transfer; accordingly, the information is left on the base substrate.

Figure 1C